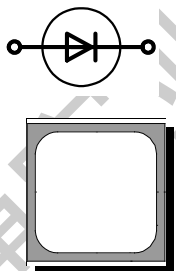


Type	Ag* Al*	V _{DRM} / V _{R_{RM}}	I _{F(AV)} [A]	Chip Size [mm] x [mm]	Package Options
DWP 9	<input checked="" type="checkbox"/> <input checked="" type="checkbox"/>	1600	20	3.90 3.90	sawn on foil <input checked="" type="checkbox"/> unsawn wafer <input checked="" type="checkbox"/> * in waffle pack <input checked="" type="checkbox"/>

*Frontside options

*Please contact IXYS chip sales



Mechanical Parameters

Area active	6.45 mm ²
Area total	15.21 mm ²
Wafer size Ø	150 mm
Thickness	265 µm
Material	Si
Max. possible chips per wafer	888
Passivation front side	Glassivation
Metallization top side	solderable: Al / Ti / Ni / Ag *
top side	bondable: Al
Metallization backside	solderable (only): Al / Ti / Ni / Ag *
Recom. wire bonds (Al)	Number 4
	Ø 380 µm
Reject Ink Dot Size	Ø 0.4-1.0 mm
Recom. Storage Environment	
sawn on foil	in org. container, in dry nitrogen < 6 month
unsawn wafer	in org. container, in dry nitrogen < 2 year
in waffle pack	in org. container, in dry nitrogen < 2 year
T	-40 ... 40 °C

Features

- planar technology
- anode top
- glassivation
- soft recovery rectifier diode

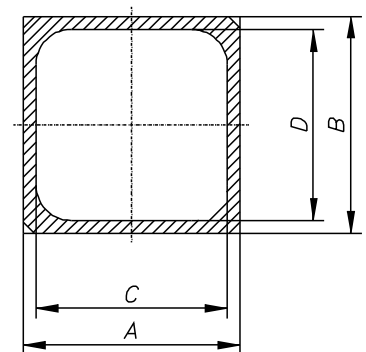
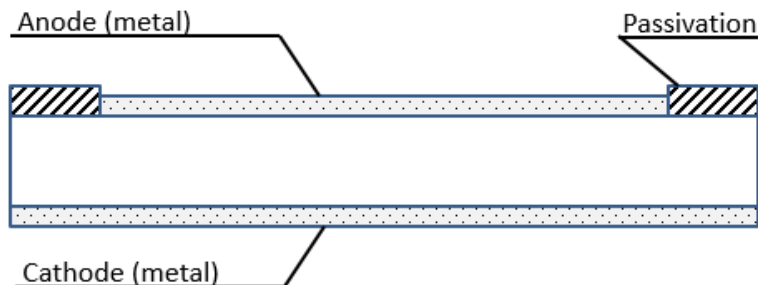
Applications

- DC Power Supplies
- Field Supply for DC motors
- Battery DC Power Supplies
- Power Rectifiers

*Sinterable top/bottom side on request

Dimensions

A	B	C	D
[mm]	[mm]	[mm]	[mm]
3.90	3.90	2.38	2.38



Electrical parameters

Symbol	Conditions	Ratings		
		min.	typ.	max.
V_D / V_R	$T_{VJ} = 25^\circ\text{C}$	1600		V
I_R	$V_R = V_{RRM}$ $T_{VJ} = 25^\circ\text{C}$			10 μA
	$V_R = 0.8 \cdot V_{RRM}$ $T_{VJ} = 150^\circ\text{C}$			1 mA
V_F	$I_F = 30 \text{ A}$ $T_{VJ} = 25^\circ\text{C}$			1.29 V
	$T_{VJ} = 150^\circ\text{C}$			1.26 V
V_{FO}	For power-loss calculations only			0.90 V
r_F	$T_{VJ} = 150^\circ\text{C}$			11.7 m Ω
T_{VJ}		-40		150 $^\circ\text{C}$
$I_{F(AV)}$ *	$T_C = 100^\circ\text{C}$ 180° rect. $T_{VJ} = 150^\circ\text{C}$			20 A
I_{FSM} *	$T_{VJ} = 45^\circ\text{C}$ t = 10 ms (50) Hz, sine			300 A
	$V_R = 0 \text{ V}$ t = 8.3 ms (60) Hz, sine			320 A
	$T_{VJ} = 150^\circ\text{C}$ t = 10 ms (50) Hz, sine			270 A
	$V_R = 0 \text{ V}$ t = 8.3 ms (60) Hz, sine			290 A
I^2t *	$T_{VJ} = 45^\circ\text{C}$ t = 10 ms (50) Hz, sine			450 A s ²
	$V_R = 0 \text{ V}$ t = 8.3 ms (60) Hz, sine			430 A s
	$T_{VJ} = 150^\circ\text{C}$ t = 10 ms (50) Hz, sine			360 A s ²
	$V_R = 0 \text{ V}$ t = 8.3 ms (60) Hz, sine			350 A s ²
R_{thJC} *	DC current			1.80 K/W

* Data according to assembled Chip

(soldered chip)

Data according to IEC 60747

Terms of Conditions and Usage

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Should you intend to use the product in aviation applications, in health or life endangering or life support applications, please notify. For any such applications we urgently recommend

- to perform joint risk and quality assessments;
- the conclusion of quality agreements;
- to establish joint measures to ensure application specific product capabilities and notify that IXYS may delivery dependent on the realization of any such measures.